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Correction: Effective strategies for current boosting in a mesa-shaped In–Ga–Zn–O vertical-channel thin-film transistor with a short-channel length of 40 nm

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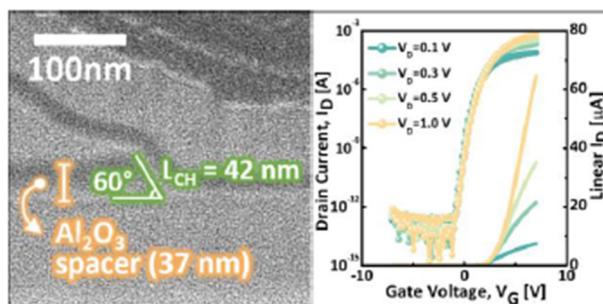
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The authors regret errors in the right y-axis label values in the published article for the graphical abstract, Fig. 2(a)–(c) and 8(a), where the displayed range of 0–800 for linear drain current should be 0–80. These errors do not impact any of the conclusions of the article.

The corrected images are shown here (the captions remain unchanged).

Graphical abstract:



The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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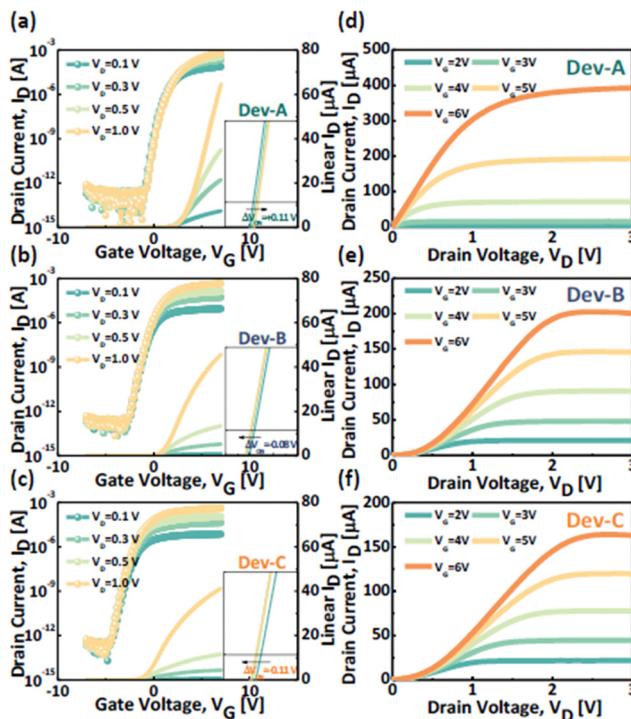


Fig. 2 Variations in transfer characteristics as an increase in V_{DS} from 0.1 to 1.0 V for the (a) Dev-A, (b) Dev-B, and (c) Dev-C, respectively. Typical output characteristics for the fabricated IGZO VCTs when the T_{CH} was varied to (d) 5 (Dev-A), (e) 10 (Dev-B), and (f) 15 nm (Dev-C), respectively.

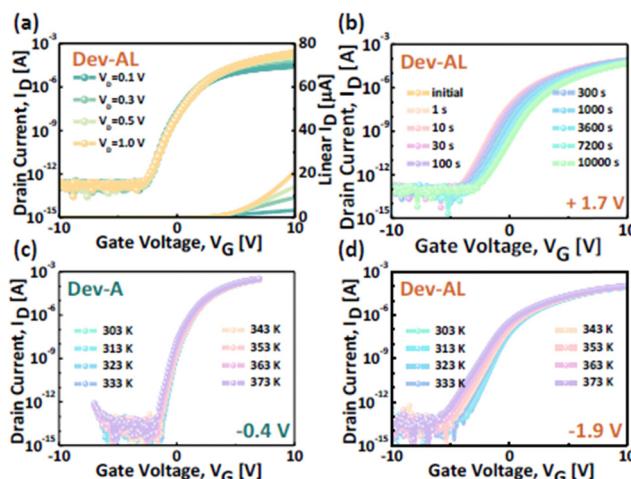


Fig. 8 Variations in transfer characteristics (a) with an increase in V_{DS} from 0.1 to 1.0 V and (b) with a lapse of stress time for 10⁴ s under the PBTS conditions at 60 °C for Dev-AL. Evolution of the transfer characteristics with an increase in measurement temperature for (c) Dev-A and (d) Dev-AL.